

# MMBTA92L, SMMBTA92L, MMBTA93L

## High Voltage Transistors

### PNP Silicon



ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)

#### Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

Rating	Symbol	92	93	Unit
Collector–Emitter Voltage	$V_{CEO}$	-300	-200	Vdc
Collector–Base Voltage	$V_{CBO}$	-300	-200	Vdc
Emitter–Base Voltage	$V_{EBO}$	-5.0	-5.0	Vdc
Collector Current — Continuous	$I_C$	-500		mAdc

#### DEVICE MARKING

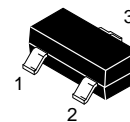
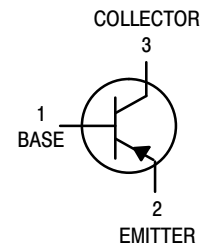
MMBTA92L, SMMBTA92L = 2D; MMBTA93LT1 = 2E

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation (Note 2) Alumina Substrate, <sup>(2)</sup> $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300	mW
		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

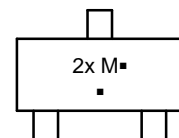
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



SOT-23 (TO-236AF)  
CASE 318  
STYLE 6

#### MARKING DIAGRAM



- 2x = Specific Device Code
- M = Date Code\*
- = Pb-Free Package

(\*Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBTA92LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
SMMBTA92LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBTA92LT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel
SMMBTA92LT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel
MMBTA93LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MMBTA92L, SMMBTA92L, MMBTA93L

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Breakdown Voltage (Note 3) ( $I_C = -1.0\text{ mA}$ , $I_B = 0$ )	MMBTA92, SMMBTA92 MMBTA93	$V_{(BR)CEO}$	-300 -200	-	Vdc
Collector–Base Breakdown Voltage ( $I_C = -100\text{ }\mu\text{A}$ , $I_E = 0$ )	MMBTA92, SMMBTA92 MMBTA93	$V_{(BR)CBO}$	-300 -200	-	Vdc
Emitter–Base Breakdown Voltage ( $I_E = -100\text{ }\mu\text{A}$ , $I_C = 0$ )		$V_{(BR)EBO}$	-5.0	-	Vdc
Collector Cutoff Current ( $V_{CB} = -200\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = -160\text{ Vdc}$ , $I_E = 0$ )	MMBTA92, SMMBTA92 MMBTA93	$I_{CBO}$	-	-0.25 -0.25	$\mu\text{A}$
Emitter Cutoff Current ( $V_{EB} = -3.0\text{ Vdc}$ , $I_C = 0$ )		$I_{EBO}$	-	-0.1	$\mu\text{A}$

## ON CHARACTERISTICS (Note 3)

DC Current Gain ( $I_C = -1.0\text{ mA}$ , $V_{CE} = -10\text{ Vdc}$ ) ( $I_C = -10\text{ mA}$ , $V_{CE} = -10\text{ Vdc}$ )  ( $I_C = -30\text{ mA}$ , $V_{CE} = -10\text{ Vdc}$ )	Both Types Both Types MMBTA92, SMMBTA92 MMBTA93	$h_{FE}$	25 40 25 25	- - - -	-
Collector–Emitter Saturation Voltage ( $I_C = -20\text{ mA}$ , $I_B = -2.0\text{ mA}$ )	MMBTA92, SMMBTA92 MMBTA93	$V_{CE(sat)}$	- -	-0.5 -0.5	Vdc
Base–Emitter Saturation Voltage ( $I_C = -20\text{ mA}$ , $I_B = -2.0\text{ mA}$ )		$V_{BE(sat)}$	-	-0.9	Vdc

## SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ( $I_C = -10\text{ mA}$ , $V_{CE} = -20\text{ Vdc}$ , $f = 100\text{ MHz}$ )		$f_T$	50	-	MHz
Collector–Base Capacitance ( $V_{CB} = -20\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	MMBTA92, SMMBTA92 MMBTA93	$C_{cb}$	- -	6.0 8.0	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

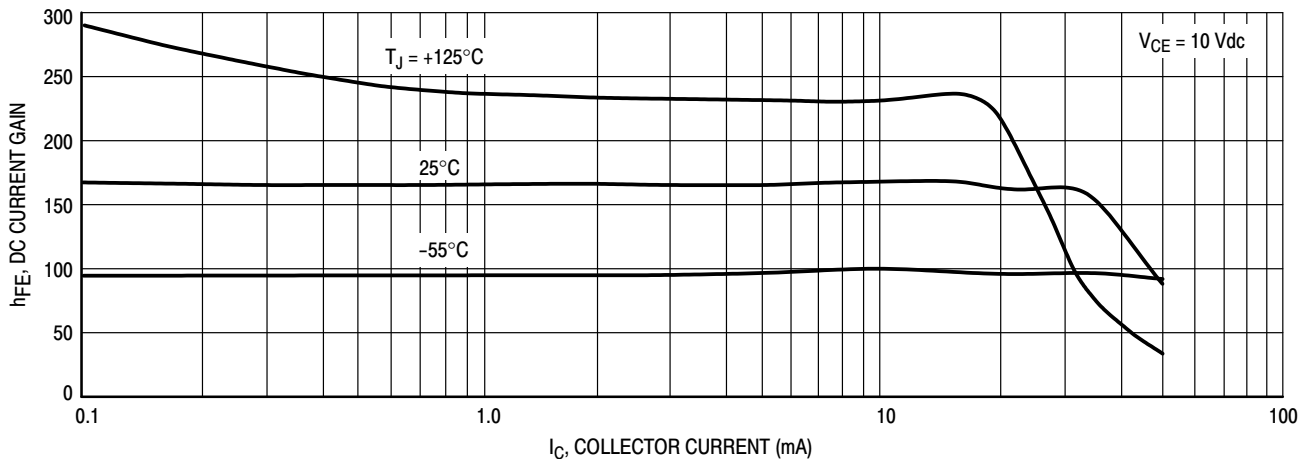


Figure 1. DC Current Gain

# MMBTA92L, SMMBTA92L, MMBTA93L

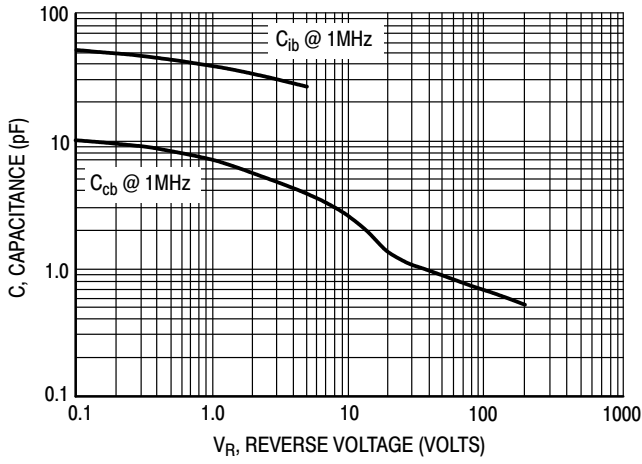


Figure 2. Capacitance

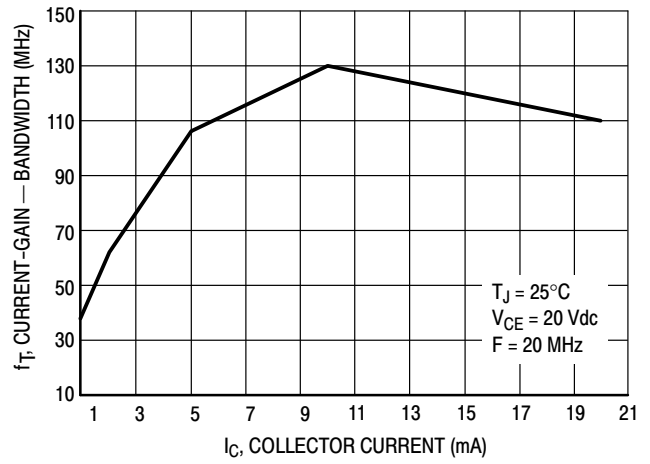


Figure 3. Current-Gain - Bandwidth

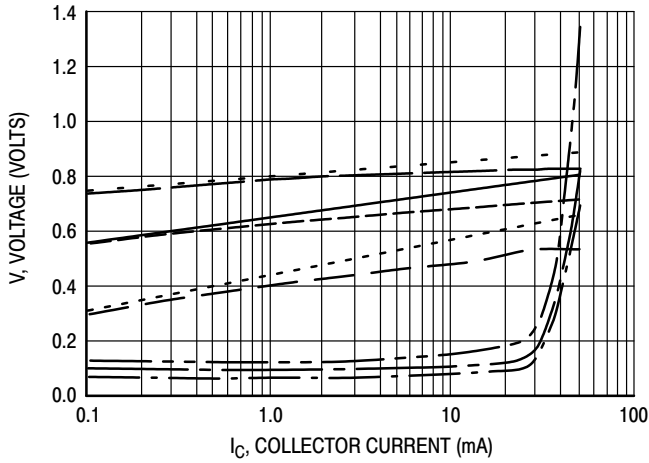


Figure 4. "ON" Voltages

- $V_{CE(sat)}$  @  $25^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{CE(sat)}$  @  $125^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{CE(sat)}$  @  $-55^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{BE(sat)}$  @  $25^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{BE(sat)}$  @  $125^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{BE(sat)}$  @  $-55^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{BE(on)}$  @  $25^\circ\text{C}$ ,  $V_{CE} = 10\text{ V}$
- $V_{BE(on)}$  @  $125^\circ\text{C}$ ,  $V_{CE} = 10\text{ V}$
- $V_{BE(on)}$  @  $-55^\circ\text{C}$ ,  $V_{CE} = 10\text{ V}$

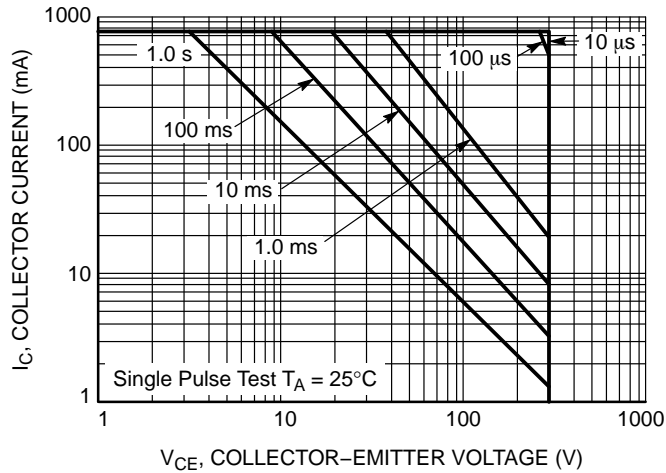


Figure 5. Safe Operating Area

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



**SOT-23 (TO-236)**  
CASE 318  
ISSUE AT

DATE 01 MAR 2023

SCALE 4:1



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H <sub>E</sub>	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**GENERIC MARKING DIAGRAM\***



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



**RECOMMENDED MOUNTING FOOTPRINT**

\* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**STYLES ON PAGE 2**

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**MECHANICAL CASE OUTLINE  
PACKAGE DIMENSIONS**



**SOT-23 (TO-236)  
CASE 318  
ISSUE AT**

DATE 01 MAR 2023

- |   |   |   |   |   |   |
|---|---|---|---|---|---|
| STYLE 1 THRU 5:<br>CANCELLED                            | STYLE 6:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 7:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR       | STYLE 8:<br>PIN 1. ANODE<br>2. NO CONNECTION<br>3. CATHODE  |   |   |
| STYLE 9:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE      | STYLE 10:<br>PIN 1. DRAIN<br>2. SOURCE<br>3. GATE     | STYLE 11:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE-ANODE | STYLE 12:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE       | STYLE 13:<br>PIN 1. SOURCE<br>2. DRAIN<br>3. GATE           | STYLE 14:<br>PIN 1. CATHODE<br>2. GATE<br>3. ANODE          |
| STYLE 15:<br>PIN 1. GATE<br>2. CATHODE<br>3. ANODE      | STYLE 16:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE | STYLE 17:<br>PIN 1. NO CONNECTION<br>2. ANODE<br>3. CATHODE | STYLE 18:<br>PIN 1. NO CONNECTION<br>2. CATHODE<br>3. ANODE | STYLE 19:<br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE-ANODE | STYLE 20:<br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE          |
| STYLE 21:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN       | STYLE 22:<br>PIN 1. RETURN<br>2. OUTPUT<br>3. INPUT   | STYLE 23:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE         | STYLE 24:<br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE           | STYLE 25:<br>PIN 1. ANODE<br>2. CATHODE<br>3. GATE          | STYLE 26:<br>PIN 1. CATHODE<br>2. ANODE<br>3. NO CONNECTION |
| STYLE 27:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE | STYLE 28:<br>PIN 1. ANODE<br>2. ANODE<br>3. ANODE     |   |   |   |   |

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